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	001447101		201 001155	Application Number		
INF	ORMATIO	N DIS	SCLOSURE	Filing Date	3 February 2004 (herewith)	
STATEMENT BY APPLICANT			PPLICANT	First Named Inventor	Hsiang Lan Lung	
				Group Art Unit		
(use as many sheets as necessary)				Examiner Name		
Sheet	1	of	2	Attorney Docket Number	MXIC 1564-1	

			U.S. PATENT DOC	JMENTS	
Examiner Initials	Cite No.1	U.S. Patent Document Number Kind Code ² (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Examiner	Cite	F	oreign Patent Do	cument	Name of Patentee or	Date of Publication of	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	Т
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INFORMATION DISCLOSURE			SCLOSURE	Filing Date	3 February 2004 (herewith)	
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Substitute for form 1449/PTO	Complete if Known			
	Application Number	10/771,023		
INFORMATION DISCLOSURE	Filing Date	3 February 2004		
	First Named Inventor	HSIANG LAN LUNG		
STATEMENT BY APPLICANT	Art Unit	Not assigned		
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U. S. PATENT DOCUMENTS Examiner Cite No.1 Document Number Publication Date MM-DD-YYYY Name of Patentee or Pages, Columns, Lines, Where Initials* Applicant of Cited Document Relevant Possages or Relevant Number-Kind Code^{2 (F Incom)} Figures Appear ^{US-} 5,515,324 EIN 05-07-1996 TANAKA US-UŞ-US US-US-US-US-US-US-US-US-IIS. US-US-US-US-US-

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Examiner Initials*	Cite No.1	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear				
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